

INFRARED DIODE LASER AT 830nm

RN-III-830R/1~500mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are widely used in measurement, spectrum analysis, etc.

产品参数

RN-III-830R/1~500mW		
Central wavelength (nm)	830±10	
Operating mode	CW	
ASE Output power (mW)	>1,10,20,...,200	>200,210, ... ,500
Power stability (rms, over 4 hours)	<1%, <2%, <3%	
Transverse mode	Round	
Beam diameter at the aperture (mm)	~2	~2
Beam divergence, full angle (mrad)	~10	~20
Warm-up time (minutes)	<5	
Beam height from base plate (mm)	24.8	
Operating temperature (°C)	10~35	
Power supply	85-264VAC	PSU-III-LED/PSU-III-FDA (Frequency for 1Hz-30kHz)
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)
TTL / Analog modulation	TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz optional	
Expected lifetime (hours)	10000	
Warranty	1 year	